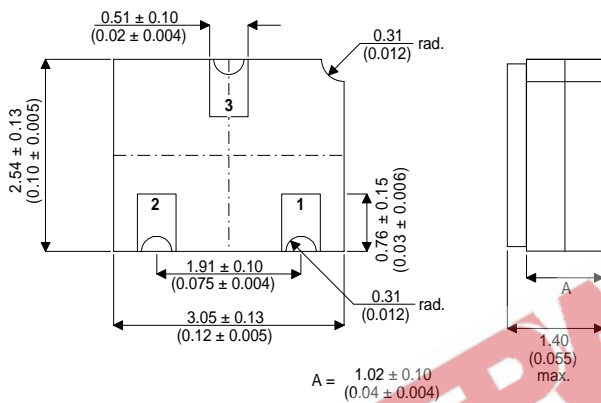


GENERAL PURPOSE NPN TRANSISTOR IN A HERMETICALLY SEALED CERAMIC SURFACE MOUNT PACKAGE FOR HIGH RELIABILITY APPLICATIONS

MECHANICAL DATA

Dimensions in mm (inches)



SOT23 CERAMIC (LCC1 PACKAGE)

Underside View

PAD 1 – Base PAD 2 – Emitter PAD 3 – Collector

FEATURES

- SILICON PLANAR EPITAXIAL NPN TRANSISTOR
- HERMETIC CERAMIC SURFACE MOUNT PACKAGE (SOT23 COMPATIBLE)
- CECC SCREENING OPTIONS
- SPACE QUALITY LEVELS OPTIONS
- HIGH SPEED SATURATED SWITCHING

APPLICATIONS:

Hermetically sealed surface mount version of the popular 2N3904 for high reliability / space applications requiring small size and low weight devices.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage	60V
V_{CEO}	Collector – Emitter Voltage	40V
V_{EBO}	Emitter – Base Voltage	6V
I_C	Collector Current	200mA
P_D	Total Device Dissipation @ $T_A = 25^\circ\text{C}$	500mW
	Derate above 25°C	$2.86\text{mW} / ^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction – Ambient	350°C/W
T_{STG}, T_J	Operating and Storage Temperature Range	-55 to $+200^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CEO}^*$ Collector – Emitter Breakdown Voltage	$I_C = 1\text{mA}$ $I_B = 0$	40			V
$V_{(BR)CBO}$ Collector – Base Breakdown Voltage	$I_C = 10\mu\text{A}$ $I_E = 0$	60			
$V_{(BR)EBO}$ Emitter – Base Breakdown Voltage	$I_E = 10\mu\text{A}$ $I_C = 0$	6			
I_{CEX} Collector – Emitter Cut-off Current	$V_{CE} = 30\text{V}$ $V_{EB} = 3\text{V}$			50	nA
$V_{CE(sat)}$ Collector – Emitter Saturation Voltage	$I_C = 10\text{mA}$ $I_B = 1\text{mA}$			0.2	V
	$I_C = 50\text{mA}$ $I_B = 5\text{mA}$			0.3	
$V_{BE(sat)}^*$ Base – Emitter Saturation Voltage	$I_C = 10\text{mA}$ $I_B = 1\text{mA}$	0.65		0.85	V
	$I_C = 50\text{mA}$ $I_B = 5\text{mA}$			0.95	
h_{FE}^* DC Current Gain	$V_{CE} = 1\text{V}$	$I_C = 0.1\text{mA}$	40		—
		$I_C = 1\text{mA}$	70		
		$I_C = 10\text{mA}$	100	300	
		$I_C = 50\text{mA}$	60		
		$I_C = 100\text{mA}$	30		

* Pulse Test: $t_p \leq 300\mu\text{s}$, $\delta \leq 2\%$.

SMALL SIGNAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
f_t Current Gain Bandwidth Product	$V_{CE} = 20\text{V}$ $I_C = 10\text{mA}$ $f = 100\text{MHz}$	300			MHz
C_{ob} Output Capacitance	$V_{CB} = 5\text{V}$ $I_E = 0$ $f = 1\text{MHz}$			4	pF
C_{ib} Input Capacitance	$V_{BE} = 0.5\text{V}$ $I_C = 0$ $f = 1\text{MHz}$			8	pF
h_{ie} Input Impedance	$V_{CE} = 10\text{V}$ $I_C = 1\text{mA}$ $f = 1\text{kHz}$	1		10	k Ω
h_{oe} Output Admittance		1		40	μhos
h_{re} Voltage Feedback Ratio		0.5		8	$\times 10^{-4}$
h_{fe} Small Signal Current Gain		100		400	—
N_F Noise Figure		$V_{CE} = 5\text{V}$ $I_C = 100\mu\text{A}$ $f = 1\text{kHz}$ $R_S = 1\text{k}\Omega$			5

SWITCHING CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_d Delay Time	$V_{CC} = 3\text{V}$ $V_{BE} = 0.5\text{V}$			35	ns
t_r Rise Time	$I_C = 10\text{mA}$ $I_{B1} = 1\text{mA}$			35	
t_s Storage Time	$V_{CC} = 3\text{V}$ $V_{BE} = 0.5\text{V}$			200	
t_f Fall Time	$I_{B1} = I_{B2} = 1\text{mA}$			50	